



环形正负电子对撞机  
Circular Electron Positron Collider



中国科学院高能物理研究所  
*Institute of High Energy Physics*  
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華中師範大學

# A compact CMOS pixel design for the CEPC vertex detector

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On behalf of the CEPC VTX study group

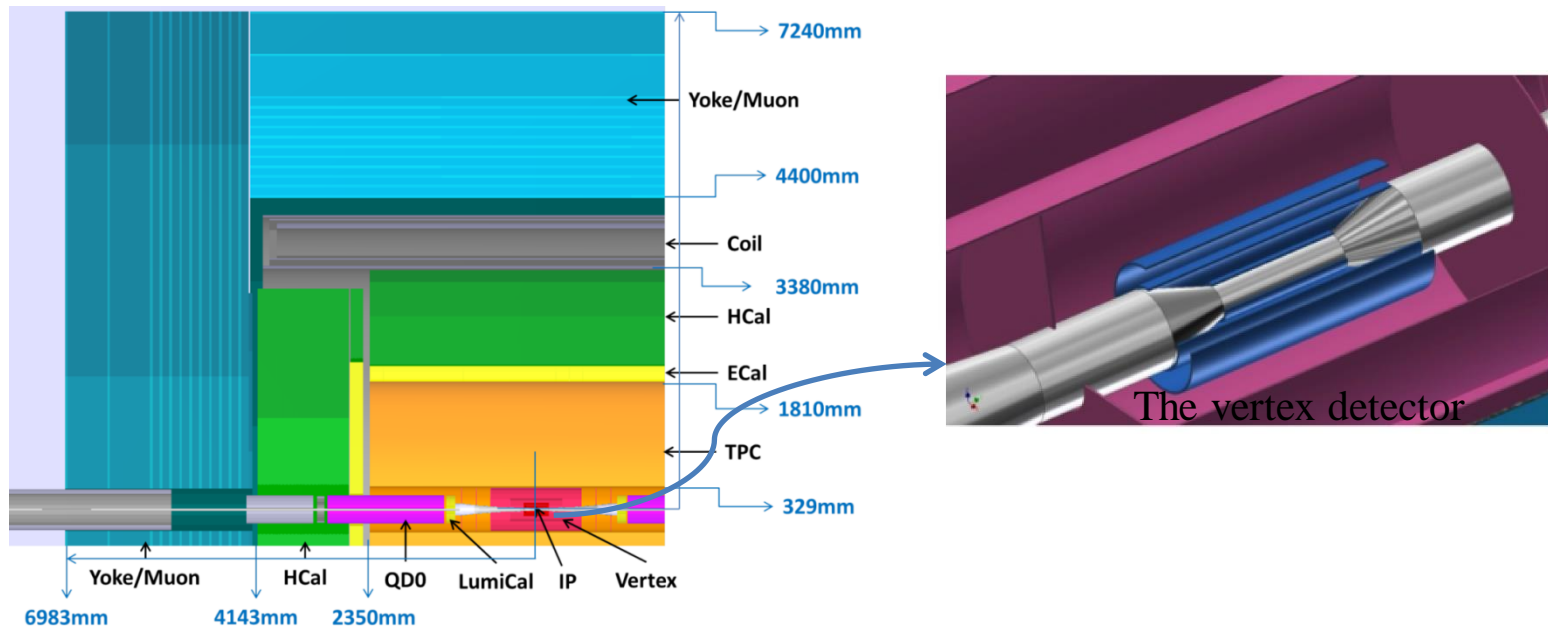
The 2019 international workshop on the high energy CEPC  
Nov, 18-20 2019

# Outline

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- CEPC vertex detector and design specifications
- CPS development and the prototypes
  - Sensitive diode study
  - First prototype of an asynchronous readout mode and test results
  - A more compact prototype design of rolling-shutter readout mode
- Summary

# Detector Layout



## Vertex detector:

- Single point resolution near the IP:  $\leq 3 \mu\text{m}$   $\rightarrow$  *high granularity*
- material budget:  $\leq 0.15\%X_0/\text{layer}$   $\rightarrow$  *Low power dissipation, thinned, monolithic pixel sensor*
- pixel occupancy:  $\leq 1\%$   $\rightarrow$  *High granularity and/or short readout time*
- Radiation tolerance:  $\sim 1\text{Mrad/y}$  (TID) and  $\sim 10^{12} \text{N}_{\text{eq}}/\text{cm}^2/\text{y}$  (NIEL)

# Design specification

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## ◆ Generally require:

- **High granularity**,  $\sigma = 3-5 \mu\text{m}$ ;
- **thin** pixel sensors with **fast readout**, readout time = **10 -100  $\mu\text{s}$**  ;
- and **low power dissipation**, Power < 100 mW/cm<sup>2</sup>

## ◆ Spatial resolution

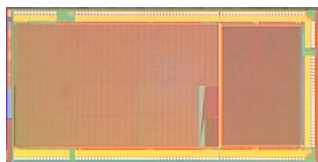
- $\frac{0.5\text{pitch}}{\sqrt{12}} < \text{S.P.resolution} < \frac{\text{pitch}}{\sqrt{12}}$
- 若 S.P.resolution = 3  $\mu\text{m}$ , **10.3  $\mu\text{m}$  < pitch < 20.7  $\mu\text{m}$**

## ◆ Low power

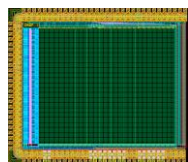
- **Binary circuit inside pixel**
- **Inside matrix zero-suppression readout, but have large pixel pitch**

# Developed CMOS Pixel Sensor prototypes for CEPC

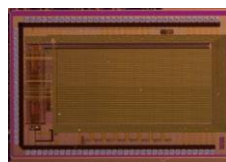
Prototype	Pixel size ( $\mu\text{m}^2$ )	Collection diode bias (V)	In-pixel circuit	R/O architecture	Main goals	Status
JadePix1	$33 \times 33$ $16 \times 16$	$< 1.8$	SF/amplifier, analog output	Rolling shutter	Sensor optimization	Lab. and beam test finished
JadePix2	$22 \times 22$	$< 10$ V (ac-coupled)	amp., discriminator, binary output	Rolling shutter	Small pixel, Power $< 100$ mW/cm <sup>2</sup>	Electrical functionality verified
MIC4	$25 \times 25$	reverse bias	Low power front-end, address encoder	Data-driven, Asynchronous	Small pixel, fast readout	Electrical functionality verified
TaiChuPix1	$25 \times 25$	reverse bias	Low power front-end, address encoder	Data-driven, Asynchronous	Small pixel, fast readout with time stamp	In measurement
JadePix3	$16 \times 26$ $16 \times 23.11$	reverse bias	Low power front-end, binary output	Rolling shutter with end of col. priority encoder	Small pixel, low power	In fabrication



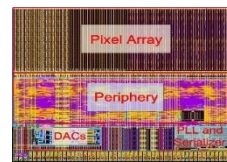
JadePix1 (IHEP)  
 $3.9 \times 7.9$  mm<sup>2</sup>



JadePix2 (IHEP)  
 $3 \times 3.3$  mm<sup>2</sup>



MIC4 (CCNU & IHEP)  
 $3.2 \times 3.7$  mm<sup>2</sup>



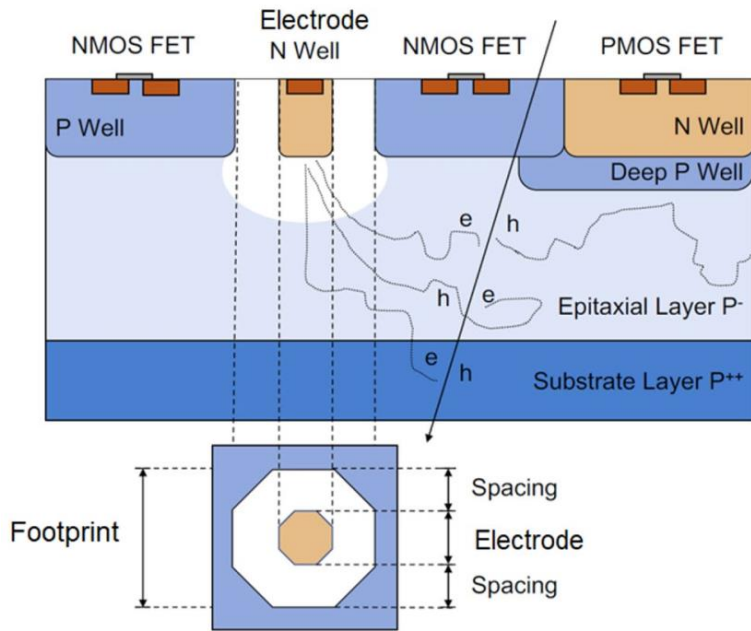
TaiChuPix1 (IHEP, SDU,  
NWPU, IFAE, CCNU)  
 $5 \times 5$  mm<sup>2</sup>



JadePix3(IHEP, CCNU,  
Dalian Minzu Univ., SDU)  
 $10.4 \times 6.1$  mm<sup>2</sup>

All prototypes in TowerJazz 180 nm CIS process

# Lower input C lower analog power



$$N \propto \frac{1}{\sqrt{g_m}} \quad S = \frac{Q}{C}$$

$$\frac{S}{N} \propto \frac{Q}{C} \sqrt{g_m} \propto \frac{Q}{C} \overset{2a\sqrt{I}}{\underbrace{g_m \propto I^{\frac{1}{a}}}}$$

$a = 2$  in strong inversion  
 $a = 1$  in weak inversion

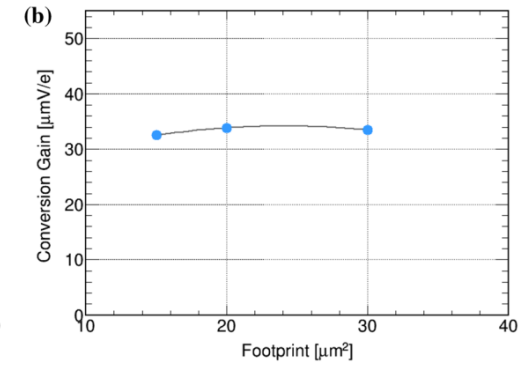
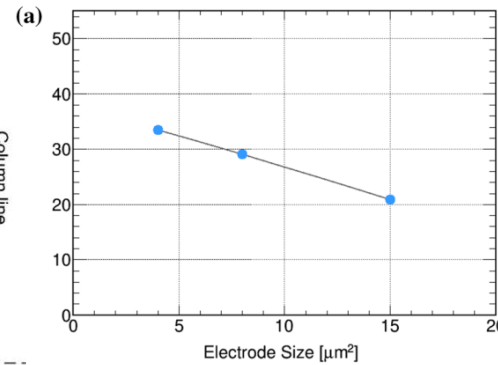
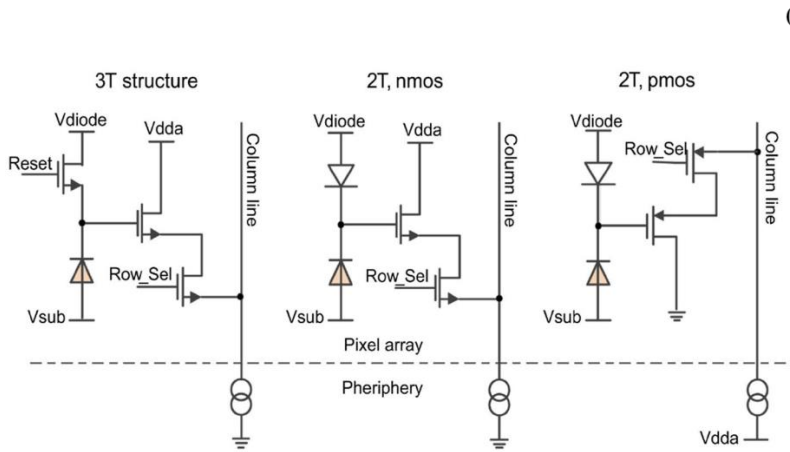
Assuming that main analog power dissipation comes from the input transistor bias

$$\rightarrow \downarrow P \propto I \propto \left( \frac{S/N}{Q/C} \right)^{2a} \uparrow \quad C \downarrow$$

Fixing the S/N for a given bandwidth  
 higher Q/C allows for a lower power

# Sensitive diode test results

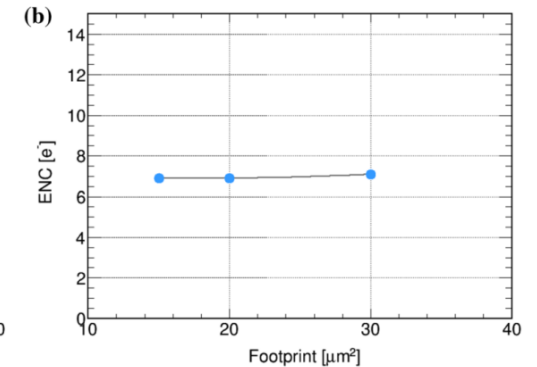
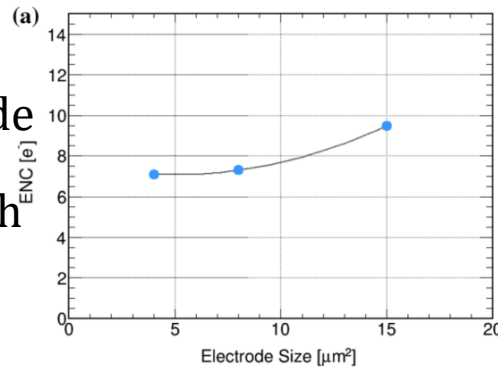
- Goals:** sensitive diode geometry optimization with JadePix1



(b) conversion gain VS. sensor geometry

(a) sensitive diode test circuit scheme

- Conclusion:** Small collection electrode size and large footprint can achieve high charge-over-capacitance ratio.

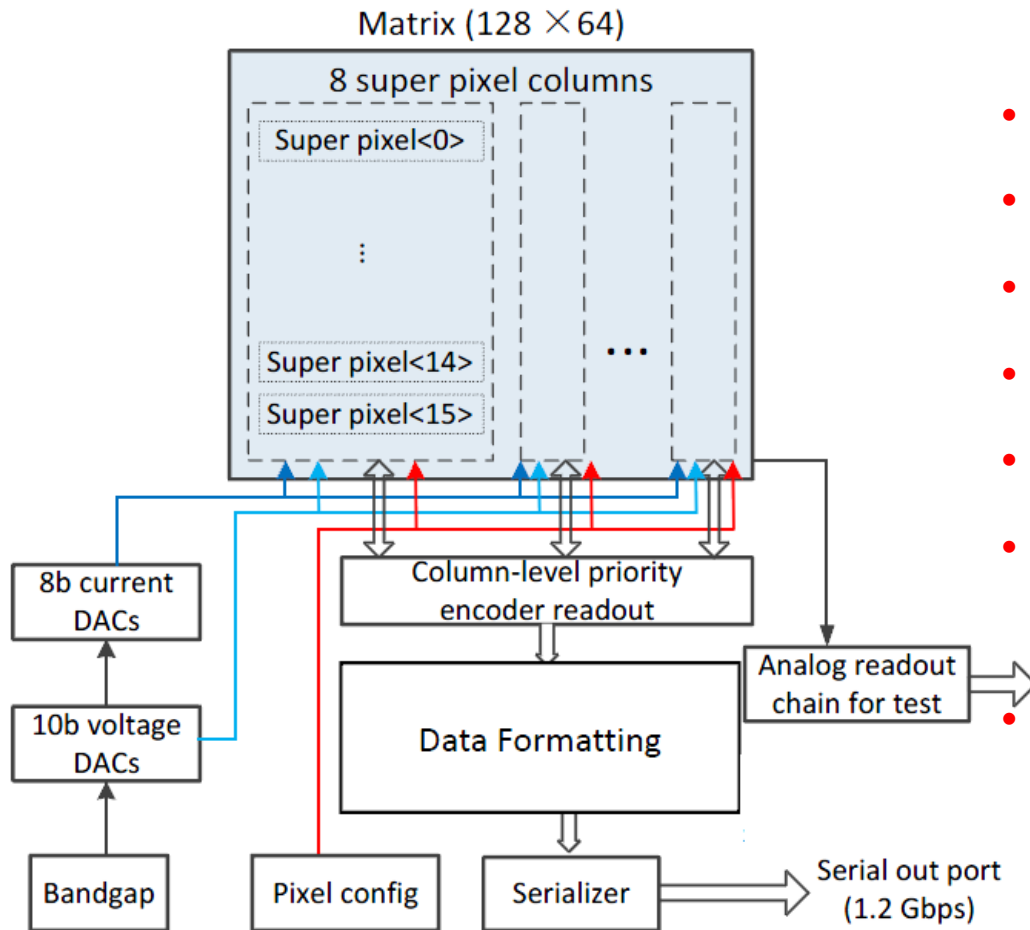


(C) ENC VS. sensor geometry

L.J.Chen, et al, RDTM (2019)  
DOI: 10.1007/s41605-019-0124-0

# First prototype MIC4 overall introduction

- Goals: ① To explore a new data-driven readout architecture which can be implemented into a small pixel size; ② Front-end study. ③ Periphery block.



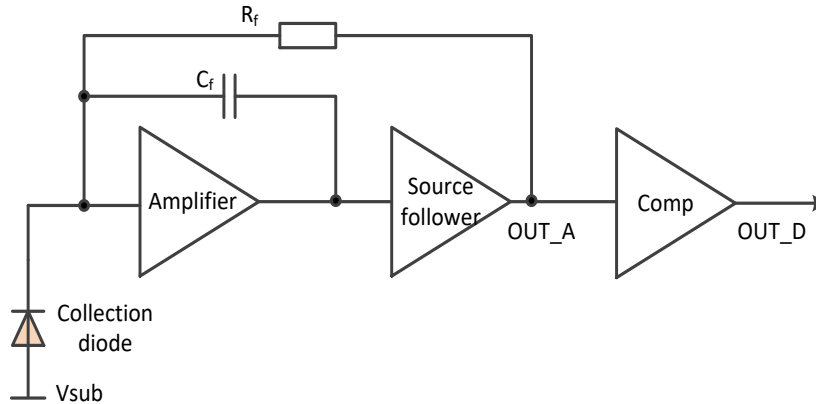
- Pixel size: 25 um x 25 um
- Matrix: 128 rows x 64 columns
- Two different front-ends in the matrix
- Zero suppression readout inside matrix
- DACs, bias
- No memory in the periphery, real time readout, serial readout rate 1.2 Gbps
- Analog test for the last row pixels

(a) MIC4 structure (MAPS IN CCNU4)

P. Yang, et al., NIM-A 924 (2019) 82-86



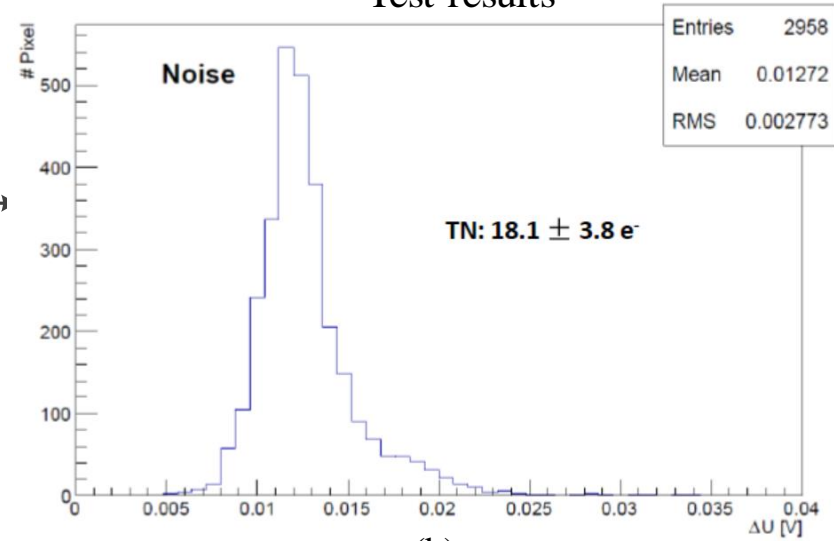
# MIC4:Pixel digital front-end version 1



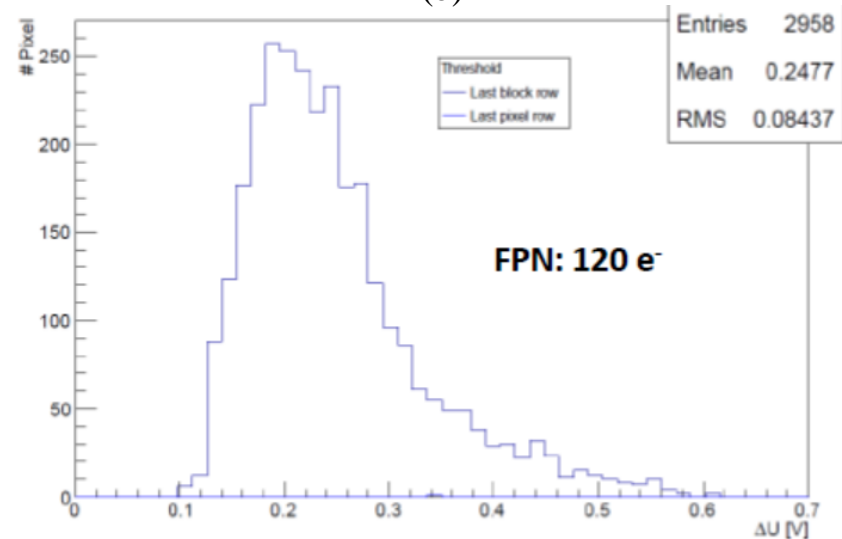
(a) CSA based analog front-end V1  
by Ying ZHANG @ IHEP

- Power cons.: 35 nW/pixel
- TN noise 18 e<sup>-</sup> is consistent with the sim results, but FPN noise 120e<sup>-</sup> is much larger than simulation (mismatch).

Test results

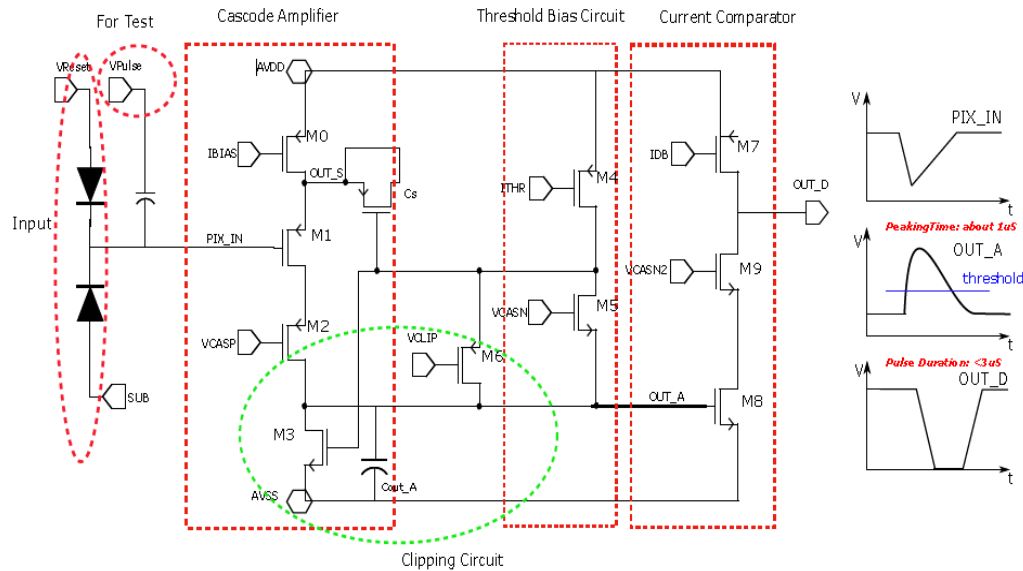


(b)



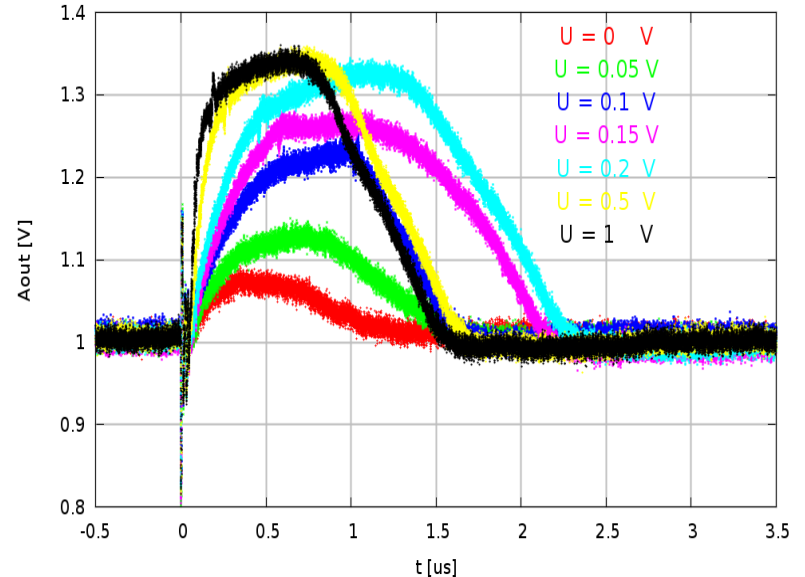
(c)

# MIC4: Pixel digital front-end version 2

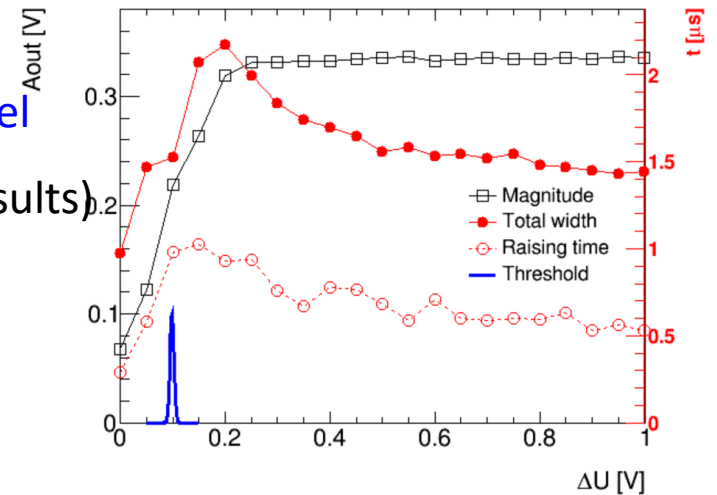


(a) Front-end V2 based on ALPIDE by Weiping Ren @ CCNU

- The ALPIDE front-end structure, Power: 110 nW/pixel
- Peaking time <math>< 1 \mu\text{s}</math>, duration <math>< 3 \mu\text{s}</math> (sim and test results)
- Mean threshold around 99 e<sup>-</sup> (test results)
- Mean FPN  $\sim 31$  e<sup>-</sup>, TN  $\sim 6$  e<sup>-</sup> (test results)

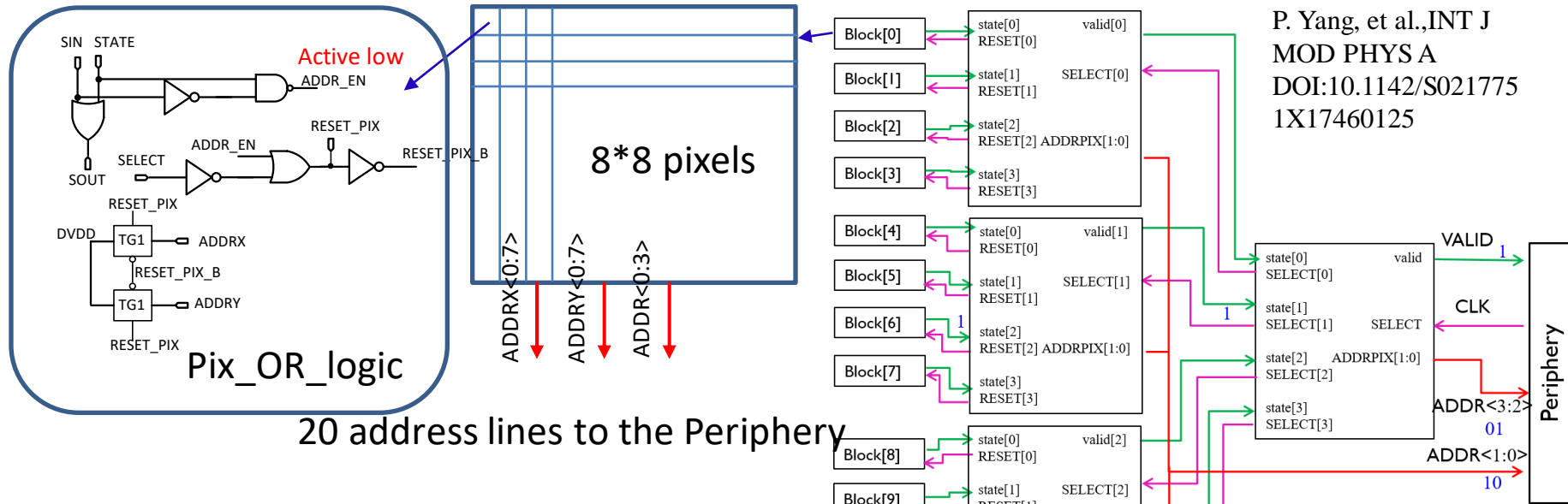


(b) OUT\_A with different VPulse voltage



(c) Test results of peaking time and duration time

# MIC4 data-driven readout scheme



P. Yang, et al., INT J  
MOD PHYS A  
DOI:10.1142/S021775  
1X17460125

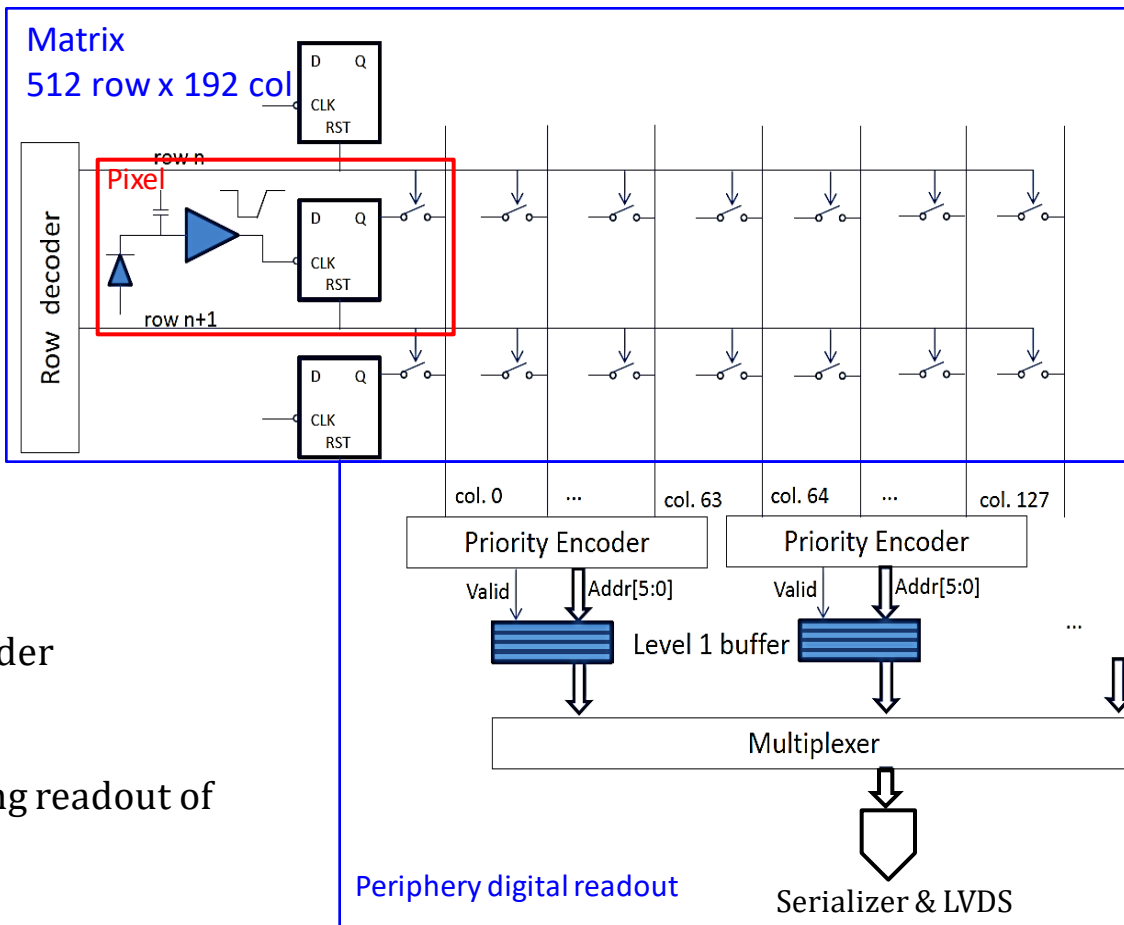
20 address lines to the Periphery

- ALPIDE matrix readout circuit AERD has many connection lines occupy large area;
- OR gate chain: speed is limited with the number of the chain pixels;
- Combine these two solutions
- Digital periphery provide a CLK signal of 60% duty cycle to enhance the readout circuit to work at 40 MHz to decode 1024 pixels; -> a few  $\mu\text{s}$  readout time

# JadePix3: Prototype of small pixel design

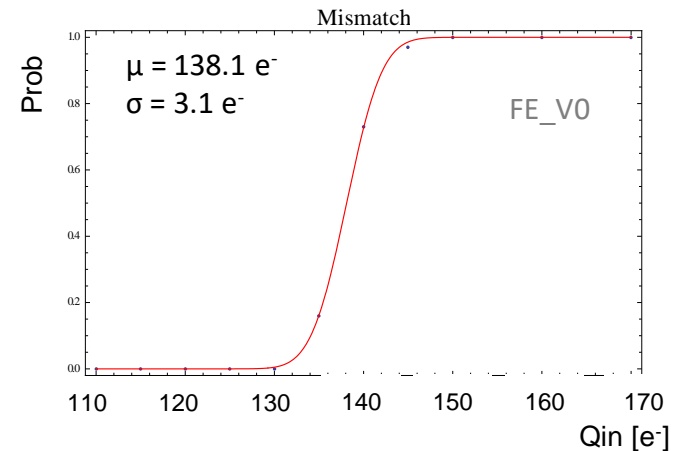
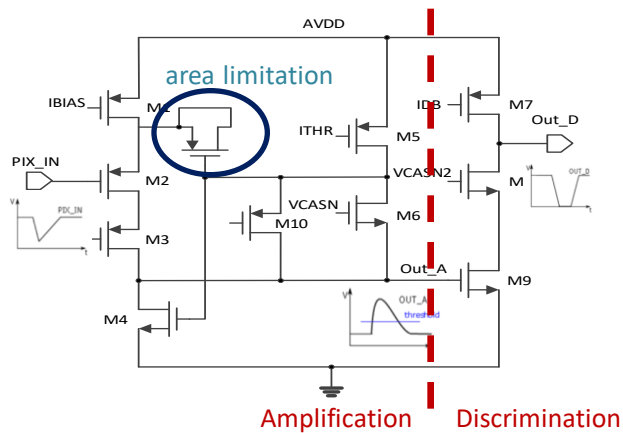
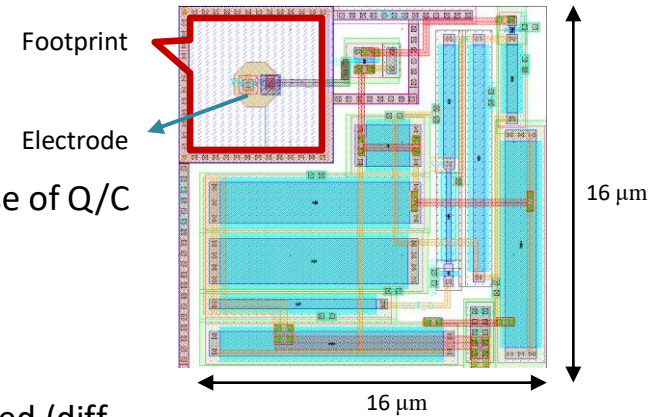
➤ Goal: Small pixel size → Low power FE + Rolling shutter Readout

- In-pixel circuit
  - Low power binary front-end
  - Optimized DFF
- Matrix Readout
  - Rolling shutter
  - 200ns/row
- Periphery digital Readout:
  - Shared column lines
  - End of column Priority Encoder
  - Zero suppression
  - 64 columns processed during readout of one row

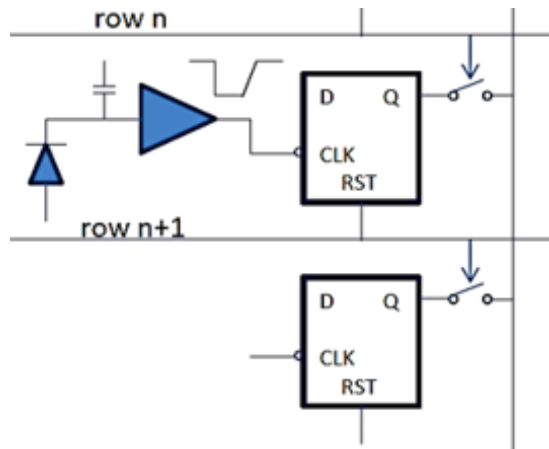


# JadePix3: Sensor & Front-end design

- Design goals: small pixel size and low power consumption
- Sensor: High Q/C (collected charge/sensor capacitance) → **low power**
  - Electrode size of  $4 \mu\text{m}^2$ , with a large footprint of  $36 \mu\text{m}^2$  → compromise of Q/C with area
- Front-end:
  - Operating principle derived from ALPIDE front end, two version designed (diff. power & peaking time)
  - Reduction on layout area,  $\sim 210 \mu\text{m}^2$
  - Improvement on the threshold dispersion (compromise with area)

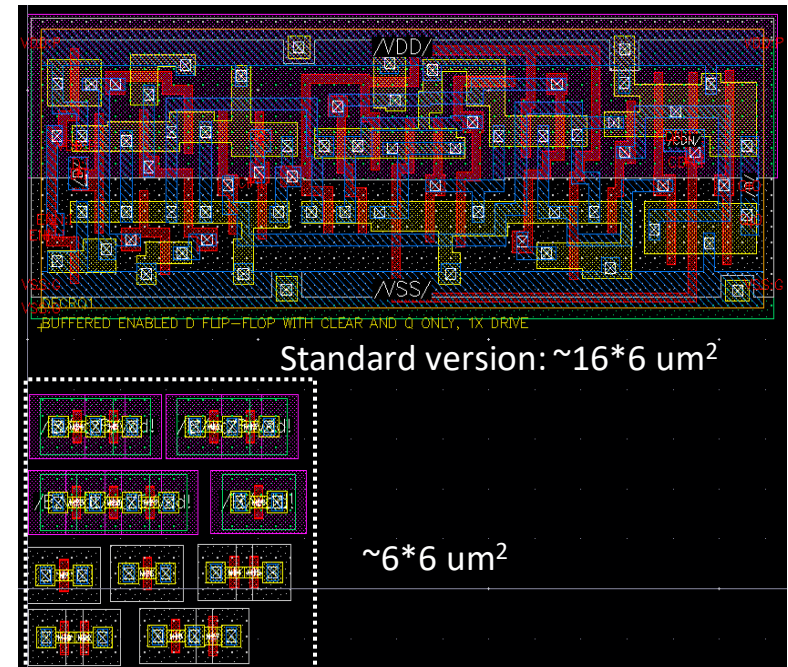


# JadePix3: DFF optimized for compact pixel



## In-pixel DFF Modified :

- Compared with standard version:
  - Transistor Num.: reduced from 36  $\rightarrow$  16
  - Layout size:  $16*6 \mu\text{m}^2 \rightarrow 6*6 \mu\text{m}^2$   
(reduced >60%)
- D connect to ground;
- Signal input from pin CLK;
- One control line shared for:
  - RST of row n / Read of row n+1



Layout of modified DFF compared with standard version

# JadePix3: Digital periphery readout

## Zero suppression at the EOC

- Priority encoder and reset decoder

- 4 bit address encoder \* 4 Sectors
- 3 Columns as one block

- Hit information 16bit:

- 9 bit row Addr. + 4bit col. Addr. + 3bit hit (one-hot code)

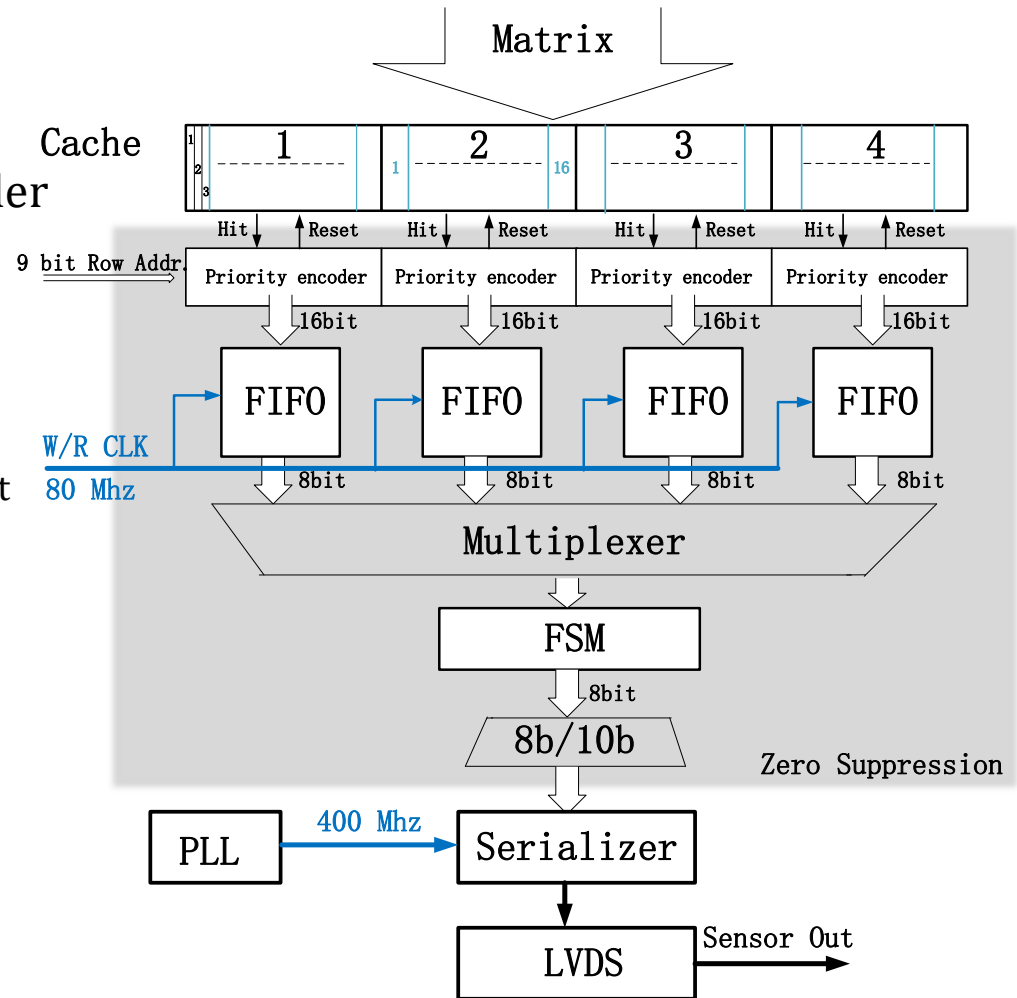
- FIFO R/W clk: 80 MHz

- FIFO depth: 48

- Data after 8b/10b : 400Mhz

- Layout: ~ 5120  $\mu\text{m}$  \* 200  $\mu\text{m}$

- Power: 15.35 mW

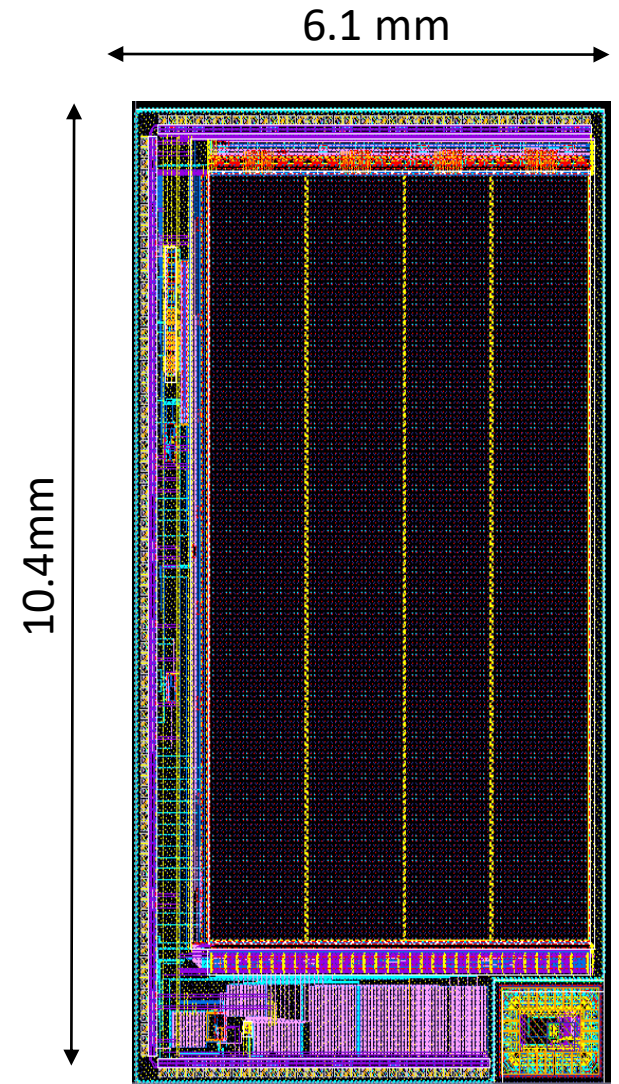


# JadePix3: Status

Team IHEP, CCNU, Dalian Minzu Univ., SDU

- Submission in Sept. 2019
- Sensitive diode, minimum size
- Front-end based on ALPIDE, but 2 versions
  - FE\_V0, FE\_V1 (9mW/cm<sup>2</sup>, 26mW/cm<sup>2</sup>)
- Pixel digital, 3 versions
  - DGT\_V0, DGT\_V1, DGT\_V2
- Pixel area
  - 16 × 26 μm<sup>2</sup>
  - 16 × 23.11 μm<sup>2</sup>

Sector	Diode	Front-end	Pixel digital	Pixel layout
0	2 + 2 μm	FE_V0	DGT_V0	16 × 26 μm <sup>2</sup>
1	2 + 2 μm	FE_V0	DGT_V1	16 × 26 μm <sup>2</sup>
2	2 + 2 μm	FE_V0	DGT_V2	16 × 23.11 μm <sup>2</sup>
3	2 + 2 μm	FE_V1	DGT_V0	16 × 26 μm <sup>2</sup>





# Summary

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- Sensitive diode geometry was studied, minimum sensitive area (JadePix1/2)
- Explored a new zero-suppression structure inside matrix, with low power front-end and almost full chip periphery blocks. All of the modules are functional. The threshold and noise was studied. (MIC4 chip)
- JadePix3 optimized the pixel size and chip periphery power consumption
  - Small pixel size, better spatial resolution expect ~3 um
- Radiation test and beam test is ongoing

Thanks to my colleagues:

IHEP: Yunpeng Lu, Ying Zhang, Yang Zhou, Zhigang Wu, Qun OuYang

CCNU: Xiangming Sun, Di Guo, Chaosong Gao, Le Xiao, Chenxing Meng,  
Anyang Xu

Dalian Minzu Univ: Zhan Shi

SDU: Liang Zhang

**Thank you for your attention!**